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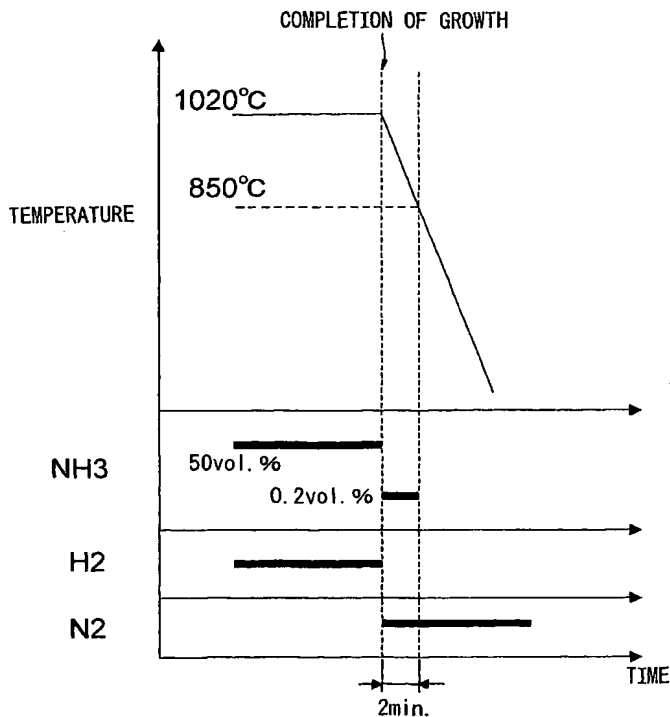
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(54) Title: P-TYPE GROUP III NITRIDE SEMICONDUCTOR AND PRODUCTION METHOD THEREOF



(57) Abstract: An object of the present invention is to provide a method for producing a p-type Group III nitride semiconductor which can be used to produce a light-emitting device exhibiting a low operation voltage and a sufficiently high reverse voltage. The inventive method for producing a p-type Group III nitride semiconductor comprises, during lowering temperature after completion of growth of a Group III nitride semiconductor containing a p-type dopant, immediately after completion of the growth, starting, at a temperature at which the growth has been completed, supply of a carrier gas composed of an inert gas and reduction of the flow rate of a nitrogen source; and stopping supply of the nitrogen source at a time in the course of lowering the temperature.



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